





DUAL N-CHANNEL ENHANCEMENT MODE FIELD EFFECT TRANSISTOR

Features

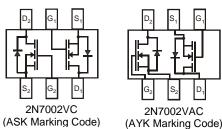
- Dual N-Channel MOSFET
- Low On-Resistance
- Low Gate Threshold Voltage
- Low Input Capacitance
- · Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 3)
- "Green" Device (Note 4)
- Qualified to AEC-Q101 Standards for High Reliability



TOP VIEW

Mechanical Data

- Case: SOT-563
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020C
- Terminal Connections: See Diagram (Note 1)
- Terminals: Finish Matte Tin annealed over Copper leadframe. Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 2
- Ordering Information: See Page 2
- Weight: 0.003 grams (approximate)



Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Units | |
|--|----------------------|------------------|------------|----|
| Drain-Source Voltage | | V_{DSS} | 60 | V |
| Drain-Gate Voltage R _{GS} ≤ 1.0MΩ | | V_{DGR} | 60 | V |
| Gate-Source Voltage (Note 2) | Continuous Pulsed | V _{GSS} | ±20 ±40 | V |
| Drain Current (Note 2) | Continuous | I _D | 280 | mA |
| Drain Current (Note 2) | Pulsed | I _{DM} | 1.5 | A |

SOT-563

Thermal Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Units |
|---|----------------------------------|-------------|-------|
| Total Power Dissipation | P_d | 150 | mW |
| Thermal Resistance, Junction to Ambient | $R_{	hetaJA}$ | 833 | °C/W |
| Operating and Storage Temperature Range | T _{j,} T _{STG} | -55 to +150 | °C |

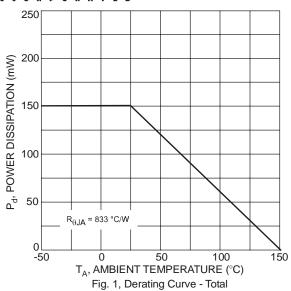
Electrical Characteristics @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Test Condition |
|---|----------------------|-----|-----|-------------|------|--|
| OFF CHARACTERISTICS (Note 5) | | | | | | |
| Drain-Source Breakdown Voltage | BV _{DSS} | 60 | 70 | _ | V | $V_{GS} = 0V, I_{D} = 10mA$ |
| Zero Gate Voltage Drain Current @ $T_C =$ @ $T_C =$ | Inco | _ | _ | 1.0 500 | μΑ | V _{DS} = 60V, V _{GS} = 0V |
| Gate-Body Leakage | I _{GSS} | _ | | ±100 | nA | $V_{GS} = \pm 20V, V_{DS} = 0V$ |
| ON CHARACTERISTIC (Note 5) | | | | | | |
| Gate Threshold Voltage | V _{GS(th)} | 1.0 | | 2.5 | V | $V_{DS} = V_{GS}, I_D = 250 \mu A$ |
| Static Drain-Source On-Resistance | R _{DS (ON)} | | | 7.5 13.5 | Ω | $V_{GS} = 5V$, $I_D = 0.05A$, $V_{GS} = 10V$, $I_D = 0.5A$, $T_j = 125$ °C |
| On-State Drain Current | | 0.5 | 1.0 | | Α | V _{GS} = 10V, V _{DS} = 7.5V |
| Forward Transconductance | g _{FS} | 80 | _ | | mS | $V_{DS} = 10V, I_D = 0.2A$ |
| DYNAMIC CHARACTERISTICS | · - | | | | • | |
| Input Capacitance | C _{iss} | _ | | 50 | рF | |
| Output Capacitance | | _ | _ | 25 | pF | $V_{DS} = 25V, V_{GS} = 0V, f = 1.0MHz$ |
| Reverse Transfer Capacitance | | _ | _ | 5.0 | pF | |
| SWITCHING CHARACTERISTICS | | | | | | |
| Turn-On Delay Time | t _{D(ON)} | _ | | 20 | ns | $V_{DD} = 30V$, $I_D = 0.2A$, $R_L = 150\Omega$, |
| Turn-Off Delay Time | | | _ | 20 | ns | $V_{GEN} = 10V$, $R_{GEN} = 25\Omega$ |

Notes:

- 1. Package is non-polarized. Parts may be on reel in orientation illustrated, 180° rotated, or mixed (both ways).
- 2. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 3. No purposefully added Lead.
- 4. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 5. Short duration pulse test used to minimize self-heating effect.





Ordering Information (Note 6)

| Part Number | Case | Packaging |
|-------------|---------|------------------|
| 2N7002VC-7 | SOT-563 | 3000/Tape & Reel |
| 2N7002VAC-7 | SOT-563 | 3000/Tape & Reel |

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information



ASK = 2N7002VC Product Type Marking Code (See Note 1) YM = Date Code Marking Y = Year ex: R = 2004 M = Month ex: 9 = September

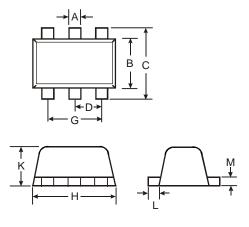


AYK = 2N7002VAC Product Type Marking Code (See Note 1) YM = Date Code Marking Y = Year ex: R = 2004 M = Month ex: 9 = September

Date Code Key

| Year | 2004 | 20 | 05 | 2006 | 2007 | 20 | 800 | 2009 | 2010 | 20 | 11 | 2012 |
|-------|------|-----|-----|------|------|-----|----------|------|------|-----|-----|------|
| Code | R | 5 | 3 | Т | U | , | V | W | Х | ` | Y | Z |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

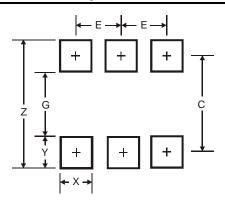
Package Outline Dimensions



| | SOT-563 | | | | | | |
|-----|----------------------|------|------|--|--|--|--|
| Dim | Min Max Typ | | | | | | |
| Α | 0.15 | 0.30 | 0.20 | | | | |
| В | 1.10 | 1.25 | 1.20 | | | | |
| С | 1.55 | 1.70 | 1.60 | | | | |
| D | 0.50 | | | | | | |
| G | 0.90 | **** | | | | | |
| Н | 1.50 | 1.70 | 1.60 | | | | |
| K | 0.55 | 0.60 | 0.60 | | | | |
| L | 0.10 | 0.30 | 0.20 | | | | |
| M | 0.10 | 0.18 | 0.11 | | | | |
| All | All Dimensions in mm | | | | | | |



Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.2 |
| G | 1.2 |
| X | 0.375 |
| Υ | 0.5 |
| С | 1.7 |
| Е | 0.5 |

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